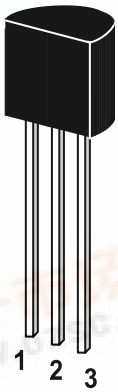


ST 2SA1505
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PNP Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into two groups, O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	35	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	30	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_{\text{C}}$	500	mA
Base Current	$-I_{\text{B}}$	50	mA
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_{j}	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{S}	-55 to +125	$^{\circ}\text{C}$

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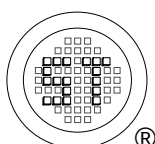
Dated : 12/12/2002

ST 2SA1505

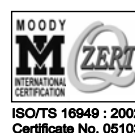
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Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}=1V$, $-I_C=100mA$					
Current Gain Group O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
at $-V_{CE}=6V$, $-I_C=400mA$					
O	h_{FE}	25	-	-	-
Y	h_{FE}	40	-	-	-
Collector Cutoff Current at $-V_{CB}=35V$	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{EB}=5V$	$-I_{EBO}$	-	-	0.1	μA
Collector Saturation Voltage at $-I_C=100mA$, $-I_B=10mA$	$-V_{CE(sat)}$	-	0.1	0.25	V
Base Emitter Voltage at $-I_C=100mA$, $-V_{CE}=1V$	$-V_{BE}$	-	0.8	1	V
Gain Bandwidth Product at $-V_{CE}=6V$, $-I_C=20mA$	f_T	-	200	-	MHz
Output Capacitance at $-V_{CB}=6V$, $f=1MHz$	C_{OB}	-	13	-	pF



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